Data Sheet, Rev 1.0, October 2019

# TLI4966G

High Precision Hall-Effect Switch with Direction Detection

Sensors



Never stop thinking

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#### TLI4966G

Revision	History:	2018-12-11	Rev 1.0
Previous	Version:		
Page	Subjects	(major changes since last revision)	

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# High Precision Hall-Effect Switch with Direction Detection

TLI4966G

# 1 Overview

#### 1.1 Features

- 2.7 V to 24 V supply voltage operation
- Operation from unregulated power supply
- High sensitivity and high stability
   of the magnetic switching points
- High resistance to mechanical stress by Active Error Compensation
- Reverse battery protection (-18 V)
- Superior temperature stability
- Peak temperatures up to 125°C without damage
- Low jitter (typ. 1 μs)
- Digital output signals
- Bipolar version
- Excellent matching between the 2 Hall probes
- Hall plate distance 1.45 mm
- Direction & speed information
- · Direction signal switches before the speed signal
- SMD package PG-TSOP6-6-9

#### 1.2 Functional Description

The TLI4966G is an integrated circuit double Hall-effect sensor designed specifically for industrial applications. Precise magnetic switching points and high temperature stability are achieved by active compensation circuits and chopper techniques on chip. They provide a speed signal at Q2 for every magnetic pole pair and a direction information at Q1, which is provided before the speed signal.

Туре	Ordering Code	Package
TLI4966G	SP003330332	PG-TSOP6-6-9





#### TLI4966G

#### Overview

### **1.3 Pin Configuration** (top view)



#### Figure 1 Pin Definition and Center of Sensitive Area

#### Table 1 Pin Definitions and Functions PG-TSOP6-6-9

Pin No.	Symbol	Function			
1	Q2	Speed			
2	GND	Recommended connection to GND			
3	Q1	Direction			
4	Vs	Supply voltage			
5	GND	Recommended connection to GND			
6	GND	Ground			



#### General

# 2 General

#### 2.1 Block Diagram



#### Figure 2 Block Diagram

#### 2.2 Circuit Description

The chopped Double Hall Switch comprises two Hall probes, bias generator, compensation circuits, oscillator, and output transistors.

The bias generator provides currents for the Hall probes and the active circuits. Compensation circuits stabilize the temperature behavior and reduce technology variations.

The Active Error Compensation rejects offsets in signal stages and the influence of mechanical stress to the Hall probes caused by molding and soldering processes and other thermal stresses in the package. This chopper technique together with the threshold generator and the comparator ensures high accurate magnetic switching points.



#### **Maximum Ratings**

# 3 Maximum Ratings

Table 2	Absolute	Maximum	Ratings

Parameter	Symbol	Limit	Values	Unit	Conditions
		min.	max.		
Supply voltage	Vs	-18 -18 -18	18 24 26	V	for 1 h, $R_{\rm S} \ge$ 200 $\Omega$ for 5 min, $R_{\rm S} \ge$ 200 $\Omega$
Supply current through protection device	Is	-50	50	mA	
Output voltage	V <sub>Q</sub>	-0.7 -0.7	18 26	V	for 5 min @ 1.2 k $\Omega$ pull up
Continuous output current	I <sub>Q</sub>	-50	50	mA	
Junction temperature	T <sub>J</sub>	-40	125	°C	
Storage temperature	T <sub>S</sub>	-40	150	°C	
Magnetic flux density	В	-	unlimited	mT	

Note: Stresses above those listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### Table 3 ESD Protection <sup>1)</sup>

Parameter	Symbol	Limit	Values	Unit	Notes	
		min.	max.			
ESD voltage	V <sub>ESD</sub>	-	±4	kV	HBM, $R$ = 1.5 kΩ, C = 100 pF $T_A$ = 25°C	

 Human Body Model (HBM) tests according to: EOS/ESD Association Standard S5.1-1993 and Mil. Std. 883D method 3015.7



#### **Operating Range**

# 4 Operating Range

Table 4	Operating	Range
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Parameter	Symbol	L	Limit Values			Conditions
		min.	typ.	max.		
Supply voltage	Vs	2.7	-	18 24	V	1 b with $P > 200 O$
		_	_	24 26		1 h with $R_{\rm S} \ge 200 \ \Omega$ for 5 min $R_{\rm S} \ge 200 \ \Omega$
Output voltage	VQ	-0.7	-	18	V	
Ambient temperature	T <sub>A</sub>	-40		115	°C	
Output current	$I_{Q}$	0	-	10	mA	



#### **Electrical and Magnetic Parameters**

# 5 Electrical and Magnetic Parameters

Symbol	Limit Values			Unit	Conditions	
	min.	typ.	max.			
Is	4	5.2	7	mA	V <sub>S</sub> = 2.7 V 18 V	
$I_{\rm SR}$	0	0.2	1	mA	V <sub>S</sub> = -18 V	
V <sub>QSAT</sub>	-	0.3	0.6	V	<i>I</i> <sub>Q</sub> = 10 mA	
$I_{QLEAK}$	-	0.05	10	μA	for $V_{\rm Q}$ = 18 V	
t <sub>f</sub>	-	0.2	1	μs	$R_{\rm L}$ = 1.2 kΩ; $C_{\rm L}$ < 50 pF	
t <sub>r</sub>	-	0.2	1	μS	see: Figure 3 on Page 13	
fosc	-	320	-	kHz		
$f_{\rm SW}$	0	-	15 <sup>2)</sup>	kHz		
t <sub>d</sub>	-	13	-	μS		
t <sub>dc</sub>	50	200	1000	ns		
t <sub>QJ</sub>	-	1	-	μ <b>s</b> <sub>RMS</sub>	Typ. value for square- wave signal 1 kHz	
B <sub>REP</sub>	-	40	-	$\mu T_{RMS}$	Typ. value for $\Delta B / \Delta t > 12 \text{ mT/ms}$	
t <sub>PON</sub>	-	13	-	μs	$V_{\rm S} \ge 2.7 \ {\rm V}$	
	-	1.45	-	mm		
	-	100	-	K/W	PG-TSOP6-6-9	
	$I_{SR}$ $V_{QSAT}$ $I_{QLEAK}$ $t_{f}$ $t_{r}$ $f_{OSC}$ $f_{SW}$ $t_{d}$ $t_{dc}$ $t_{QJ}$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$I_{\rm S}$ 4       5.2       7 $I_{\rm SR}$ 0       0.2       1 $V_{\rm QSAT}$ -       0.3       0.6 $I_{\rm QLEAK}$ -       0.05       10 $t_{\rm f}$ -       0.2       1 $t_{\rm f}$ -       0.2       1 $t_{\rm f}$ -       0.2       1 $f_{\rm OSC}$ -       320       - $f_{\rm SW}$ 0       -       15 <sup>2</sup> $t_{\rm d}$ -       13       - $t_{\rm dc}$ 50       200       1000 $t_{\rm QJ}$ -       1       - $B_{\rm REP}$ -       40       - $t_{\rm PON}$ -       13       - $d_{\rm HALL}$ -       1.45       -	$I_{\rm S}$ 4       5.2       7       mA $I_{\rm SR}$ 0       0.2       1       mA $V_{\rm QSAT}$ -       0.3       0.6       V $I_{\rm QLEAK}$ -       0.05       10 $\mu A$ $t_{\rm f}$ -       0.22       1 $\mu s$ $t_{\rm f}$ -       0.22       1 $\mu s$ $t_{\rm f}$ -       0.2       1 $\mu s$ $f_{\rm OSC}$ -       320       -       kHz $f_{\rm OSC}$ -       320       -       kHz $f_{\rm SW}$ 0       -       15 <sup>2</sup> kHz $t_{\rm d}$ -       13       - $\mu s$ $t_{\rm QJ}$ -       1       - $\mu S_{\rm RMS}$ $B_{\rm REP}$ -       40       - $\mu T_{\rm RMS}$ $t_{\rm PON}$ -       13       - $\mu s$ $d_{\rm HALL}$ -       1.45       -       mm	

#### Table 5 Electrical Characteristics <sup>1)</sup>

1) over operating range, unless otherwise specified. Typical values correspond to  $V_{\rm S}$  = 12 V and  $T_{\rm A}$  = 25°C

2) To operate the sensor at the max. switching frequency, the magnetic signal amplitude must be 1.4 times higher than for static fields. This is due to the -3 dB corner frequency of the low pass filter in the signal path.

3) Systematic delay between magnetic threshold reached and output switching

4) Jitter is the unpredictable deviation of the output switching delay

5)  $B_{\text{REP}}$  is equivalent to the noise constant

6) Time from applying  $V_{\rm S} \ge$  2.7 V to the sensor until the output state is valid

7) Thermal resistance from junction to ambient

#### **Electrical and Magnetic Parameters**

#### Calculation of the junction temperature (PG-TSOP6-6-9 example)

e.g. for  $V_{\rm S}$  = 12.0 V,  $I_{\rm Smax}$  = 7.0 mA,  $V_{\rm QSATtyp}$  = 0.3 V and 2 x  $I_{\rm Q}$  = 10 mA : Power Dissipation:  $P_{\rm DIS}$  = 90.0 mW. In  $T_{\rm J}$  =  $T_{\rm A}$  + ( $R_{\rm thJA} \times P_{\rm DIS}$ ) / for  $T_{\rm A}$  = 115°C + (100 K / W × 0.09 W) Resulting max. junction temperature:  $T_{\rm J}$  = 124.0°C

Parameter	Symbol T <sub>j</sub> [°C]		Limit Values			Unit	Conditions
			min.	typ.	max.		
Operate point	B <sub>OP</sub>	-40 25 125	5.2 5.0 4.7	7.7 7.5 7.1	10.3 10.0 9.5	mT	
Release point	B <sub>RP</sub>	-40 25 125	-10.3 -10.0 -9.5	-7.7 -7.5 -7.1	-5.2 -5.0 -4.7	mT	
Hysteresis	B <sub>HYS</sub>	-40 25 125	- 10.0 -	- 15.0 -	- 20.0 -	mT	
Magnetic matching	B <sub>MATCH</sub>	-40 25 125	- -2.0 -	_ 0 _	- 2.0 -	mT	Valid for $B_{OP1} - B_{OP2}$ and $B_{RP1} - B_{RP2}$
Magnetic offset	B <sub>OFF</sub>	-40 25 125	- -2.0 -	- 0 -	- 2.0 -	mT	$(B_{\rm OP} + B_{\rm RP})/2$
Temperature compensation of magnetic thresholds	TC	-	-	-350	-	ppm/°C	

 Table 6
 Magnetic Characteristics <sup>1)</sup>.

1) over operating range, unless otherwise specified. Typical values correspond to  $V_{\rm S}$  = 12 V

Note: Typical characteristics specify mean values expected over the production spread.

#### **Field Direction Definition**

Positive magnetic fields related with south pole of magnet to the branded side of package.



#### Timing Diagrams for the Speed and Direction Outputs

# 6 Timing Diagrams for the Speed and Direction Outputs



Figure 3 Timing Definition of the Speed Signal







Timing Diagrams for the Speed and Direction Outputs



Figure 5 Definition of the Direction Signal

Rotation Direction	State of Direction Output $V_{\rm Q1}$
Left to right	Low
Right to left	High



**Package Information** 

# 7 Package Information

### 7.1 Package Marking





### 7.2 Distance between Chip and Package Surface



#### Figure 7 Distance Chip to Upper Side of IC



#### TLI4966G

#### **Package Information**

#### 7.3 Package Outlines



Figure 8 PG-TSOP6-6-9 (Plastic Thin Small Outline Package)

#### PCB Footprint for PG-TSOP6-6-9

The following picture shows a recommendation for the PCB layout.





You can find all of our packages, sorts of packing and others in our Infineon Internet Page "Products": http://www.infineon.com/products. Dimensions in mm

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